Low Temperature Characterization of Space Photovoltaics

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Why Low Temperature Characterization

X-Ray by Measurement

- LIV
 - Power at lower temperatures for deep space missions such as Juno and when coming out of eclipse in earth based orbits
- QE
 - Current mismatch is affected by temperature
 - Band edges shift as a function of temperature which in turn affects how much of the solar spectrum is absorbed by each junction
- Subcell IV
 - Subcell open circuit voltage
 - Subcell diode properties
 - Quantify midgap defect energy
- EL
 - Identify junction quality
 - Identify energy level of defects
- Hopefully provide more accurate data and develop models to improve on orbit performance of solar cells



Temperature Dependent LIV

Why Radiometric Calibration

- Standard method: Calibrate simulator using solar cell isotypes of a given technology at 28°C. Next, vary the temperature of the solar cell and measure LIV data
 - Historically calibration standards of multijunction junction solar cells are made from high altitude flights and their calibration values are set to be at 28C.
- Problems with Standard method:
 - The simulator is not a good "Constant".
 The spectrum of the lab looks very different than AM0
 - As the absorption properties of the solar cell change, how much light they see from a simulator changes as well.
 Because the simulator spectrum is not a good match to AM0 this can introduce error
- By using radiometric calibration we can alleviate this problem





Radiometric Calibration

- Radiometric calibration uses a spectroradiometer to measure the spectrum of the simulator
- Quantum efficiency measurements of monolithic multijunction solar cells are used to tune the spectrum of the simulator instead of isotypes
 - Effectively mimics isotypes without the need of isotypes
- A set of filters to tune the color spectrum of the lamp and iris to tune the intensity allow for the ability to tune up to 6 zones on our X-25 solar simulator



Tuning for Temperatures

Tuning Radiometrically



- Solar simulator was tuned for each temperature as referenced to E490 AM0
- Results in a different solar simulator spectrum for each temperature

Difference between each Simulator Spectrum



- All simulator spectra were normalized to the 300K tune
- Most of the spectral differences are in the J2 and J3
- Spectrum can be up to 15% off

How well does radiometric match AM0?

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J_{5C} (mA/cm²) 0 R R P2

18

- Pretty well....better than not tuning radiometrically
- Tuning for each temperature allows almost a near perfect match to E490
- If you only tune for one temperature (300K in this case), the cell ends up being J3 limited at 80K
 - Normalized to AM0 (%) 0 -2 -4 11: SolSim 300K 12: SolSim 300K -6 13: SolSim 300K • J1: SolSim Temp ·• J2: SolSim Temp O- 13: SolSim Temp 100 150 200 250 300



Normalized to AM0

Temperature (K)

Temperature (K)

200

11: E490

J3: E490 J1: SolSim 300K

J2: SolSim 300K J3: SolSim 300K

11: SolSim Temp

J3: SolSim Temp

300

· O · 12: SolSim Temp

- I2: E490

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250



- J1 was a close match to AM0 regardless of method
- This is the case with our simulator and represents potential lab-to-lab differences

LIV

- Current decreases and voltage increases with decreasing temperatures...as expected
- Fill Factor rises, maxing out at 150K and begins to decrease
- Efficiency reaches a maximum of > 36% at 80K from 28% at 300K



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Balloon Calibration vs Radiometric Calibration

- Radiometric tuning allows for an accurate determination of efficiency at lower temperatures
- If we tune using the standard method the efficiency actually goes down at lower temperatures
- Also the short circuit current produced from the standard method and radiometric is very different. The balloon calibration tune yields lower currents
 - Still investigating the cause for this



Subcell Characterization



Low Temperatures Subcell I-V

- As seen in the LIV the subcell I-V shifts to higher voltage at lower temperatures
- A tunnel defect appears to show up at lower temperatures for J1 and J2
- Lines through points represents fits to diode equation
- Future analysis will look into the midgap energy and change in ideality with temperature and compared to post radiation testing





- The top cell EL intensity behaves contrary to typical III-V direct and indirect materials.
 - Luminescence intensity decreases with decreasing temperatures.
 - The peak band energy blue shifts as expected.
 - At temperatures below 120K the luminescence intensity begins to increase and low energy shoulder begins to appear.
 - Behavior has been observed in higher bandgap InGaP materials with a large Ga content [1]
 - A possible reason for the EL behavior could be due to ordered and disordered layers in the InGaP top layers [2]
- Middle cell behaves exactly as expected
 - At lower temperatures a low energy defects begins to appear
 - Intensity increase stabilizes
- Bottom cell intensity behaves similar to the top cell due to its indirect nature
 - Broad band emission is due to diffusion of Ge and dopants between the middle and Ge bottom cell [3]

[3] G. Brammertz et al., "Low-temperature photoluminescence study of thin epitaxial GaAs films on Ge substrates," J. Appl. Phys., vol. 99, no. 9, 2006

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^[1] C. Wang, B. Wang, R. I. Made, S.-F. Yoon, and J. Michel, "Direct bandgap photoluminescence from n-type indirect GaInP alloys," *Photonics Res.*, vol. 5, pp. 239–244, 2017 [2] L. Bhusal *et al.*, "Ordering induced direct-indirect transformation in unstrained Ordering induced direct-indirect transformation in unstrained GaxIn1-xP for $0.76 \le x \le 0.78$," vol. 114909, pp. 1–4, 2009

Lots more to do

Conclusions

- Radiometric calibration allows for accurate low temperatures LIV measurements that match well to AM0
- Obtained low temperature quantum efficiency of multijunction solar cells
- Demonstrated measurement of low temperature subcell current-voltage curves
- Identified potential disorder in top cell as well as finally figured out the origin of the broadband luminescence in the IR luminescence
- Next Step
 - Perform defect energy analysis using luminescence, DIV, and subcell I-V data
 - Irradiate solar cell and see what happens
 - We know the ideality changes but now we want to see what defects show up in EL and energy of those defects
 - Perform annealing studies to see how the defects stay or go away
 - Ultimately relate this to some model to better predict radiation degradation in solar cells